



TestConX 中国
China™

October 29, 2019

InterContinental Shanghai Pudong Hotel

Archive

HAST In-Situ Electrical Tests Down-to Pico-Ampere Range

Yi-Ming Lau and Choon-Leong Lou
STAr Technologies, Inc.



Shanghai • October 29, 2019



Contents

- Background
- Industrial Requirements
- Objectives
- Experimental Setup & Conditions
- Key Parameters & Considerations
- Experimental Data & Results
- Conclusions
- Acknowledgements



HAST In-Situ Electrical Tests Down-to Pico-Ampere Range

2019

2

Background

- Traditional HAST or THB
 - Stress devices in chamber at high voltage, high temperature & high humidity
 - At predetermined stress time, devices are powered down and cooled back to ambient temperature
 - Devices are tested outside chamber using an external electrical test system for low level current at precision biased voltage
 - After measurement, devices are put back to the chamber and powered back again to HAST or THB conditions to continue to the next cycle
- Disadvantages
 - Quality issue and human error due to transportation of burn-in board
 - Time consuming, high operational overhead and high cost
 - Lack of real-time test results on the functionality and performance of devices during stress resulting in wastage of stress-hours on damaged devices

Industrial Requirements

- Industrial Requirements
 - More devices require low-level pico-ampere current tests such as off-state current at wide varying voltages (V ~ KV)
 - Real time electrical data is required to understand the device performance during the long stress cycle
 - Enabling experiments to be stopped as and when devices failed, not until the end of the required stress setup.
- Problem Faced
 - There are no sockets, DUT boards & cable assemblies capable of supporting tests at low level pico-ampere current measurements within high temperature and high humidity chamber
 - Requirement of long lifetime sockets, DUT boards & cable assemblies enabling lower cost of burn-in tests



HAST In-Situ Electrical Tests Down-to Pico-Ampere Range

2019

4

Objectives

- Objectives
 - Qualified set of DUT Board, socket & cable assemblies fully capable to work under high temperature & high humidity
 - Provide low leakage electrical measurements with leakage current down to 10pA/V level under high temperature and high humidity burn-in stress tests
 - Demonstrate in-situ electrical measurements during HAST /THB data with the DUT Board, socket & cable assemblies in high temperature and high humidity chamber
 - Minimal degradation and/or recoverable DUT boards, sockets & cable assemblies

Experimental Setup & Conditions

- Experiment Setup
 - DUT Board with Sockets and Cable Assemblies
 - Half the channels are in controlled conditions and the other half are under normal (exposed) conditions
 - Environment Conditions: 85°C/85% RH
- Measurements / Read points
 - Sweep measurements from -20V to +20V (1V step)
 - Leakage = Last Point Current / +20V
 - Read Intervals: 0.5hr
- Experiment to Simulate In-Situ & External Data Correlation
 - Oven was POWER DOWN at ~29th hour
 - Oven is POWER ON again at ~34th hour



HAST In-Situ Electrical Tests Down-to Pico-Ampere Range

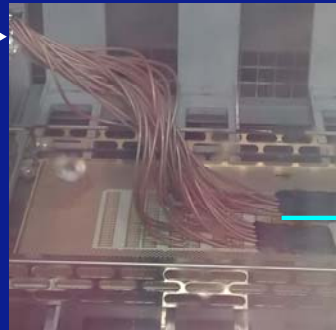
2019

6

Experimental Setup & Conditions

Test & Measurement System

- Source-measurement unit (SMU) with current measurements at resolution down to fA level



Shielded Coaxial Cables connected to shielded ceramic DUT board with traces to DUT Sockets for measurements down-to pico-Ampere levels



High-temperature & high humidity burn-in chamber

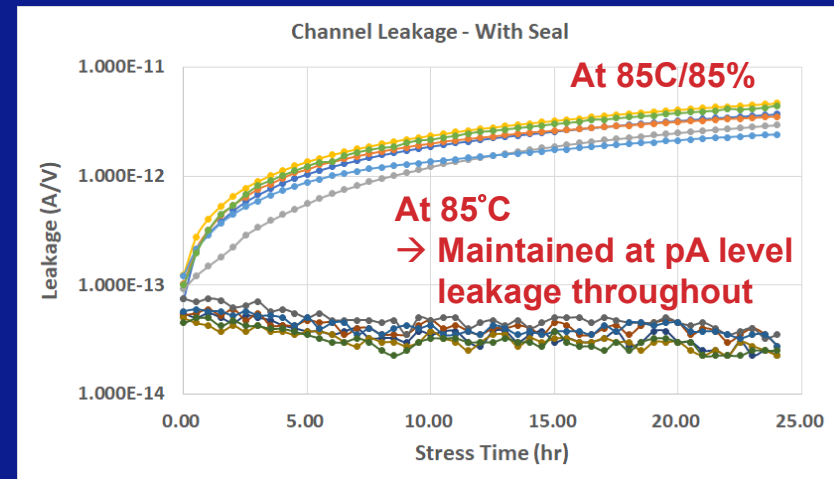
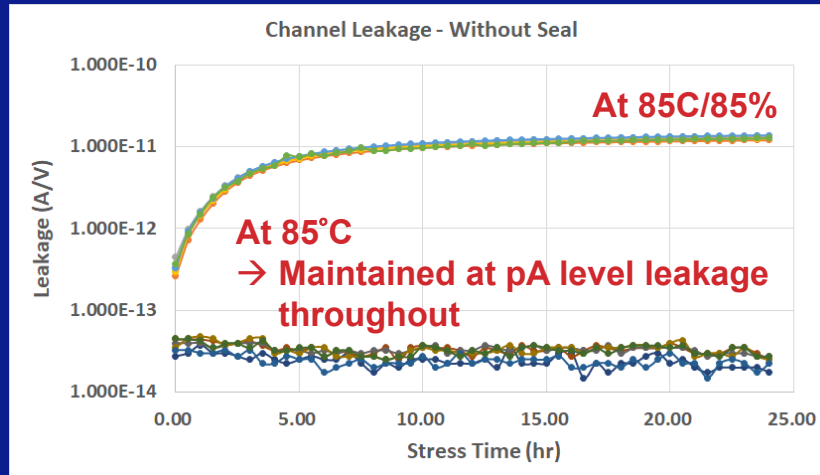
Key Parameters & Considerations

Key Parameters:

- Channel leakage is well-controlled at $<1\text{pA/V}$ at 85°C over 24hrs
- But Channel leakage will increase over time under $85^\circ\text{C}/85\%$ RH condition
- Key Parameter for HAST/THB: HUMIDITY

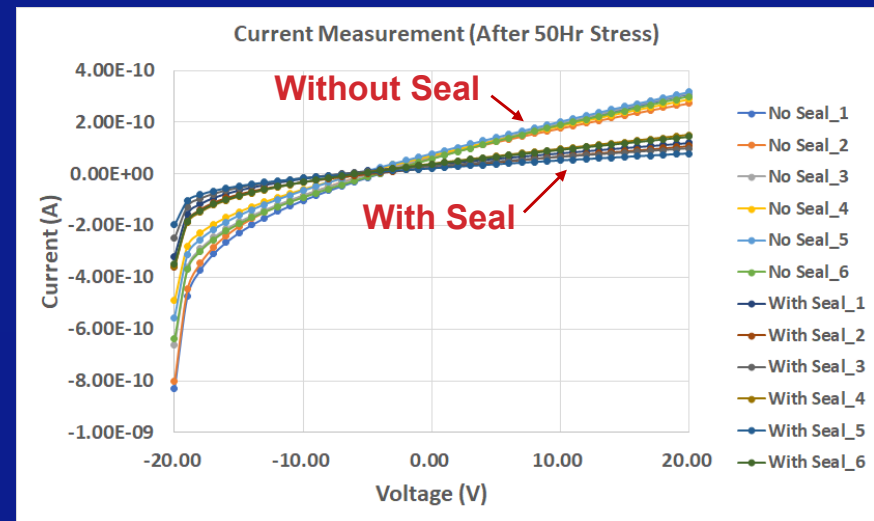
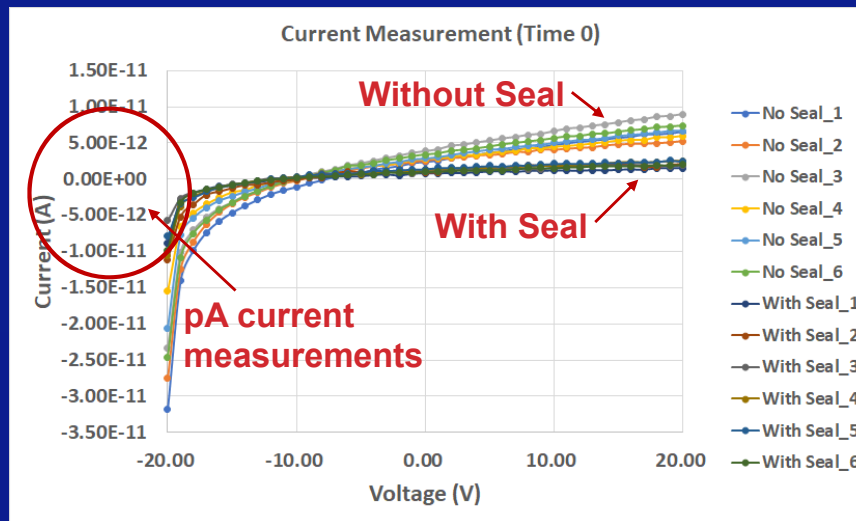
Key Considerations:

- Channel leakage to stabilize over time
- Leak to be maintained at pA level over time
→ In-situ pA level current measurements over long hours is possible

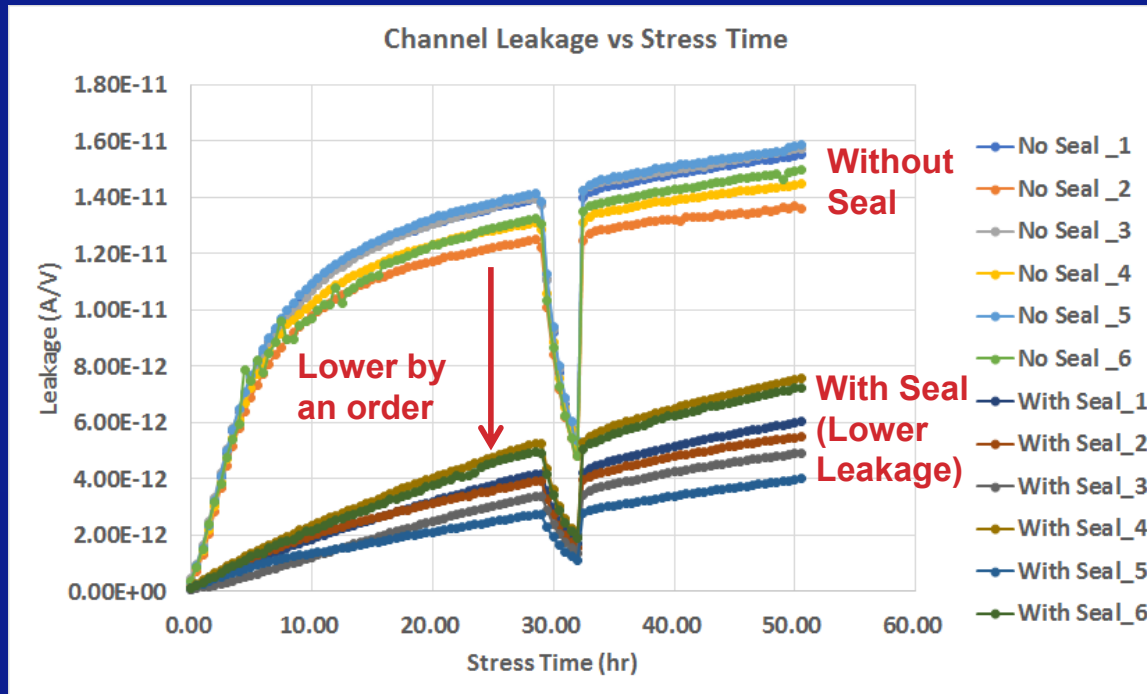


Pico-Ampere Current Measurements

- IV data showing pA current measurements for each channel at Time 0hr & 50Hr
- Test & Measurement System exhibit the capability of pA current measurements during stress at 85°C and 85%RH



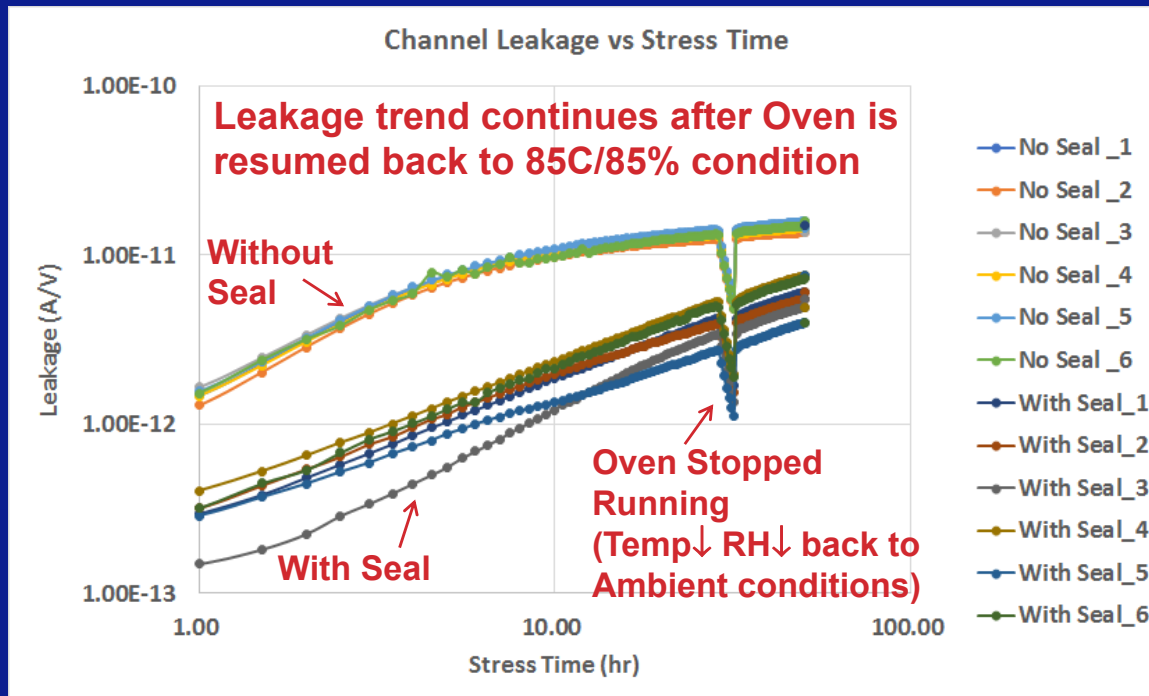
Low Leakage During 85°C/85% RH



Channel Leakage at 85°C/85%RH
(a) Leakage (w/o Seal): ~16pA/V
(b) Leakage (w Seal): ~0.8pA/V

- pA leakage level is achievable at 85C/85% RH conditions using the DUT Board, Socket & Cable Assembly
- Sealing can effectively reduce the leakage down to pA level

In-Situ Electrical Measurements



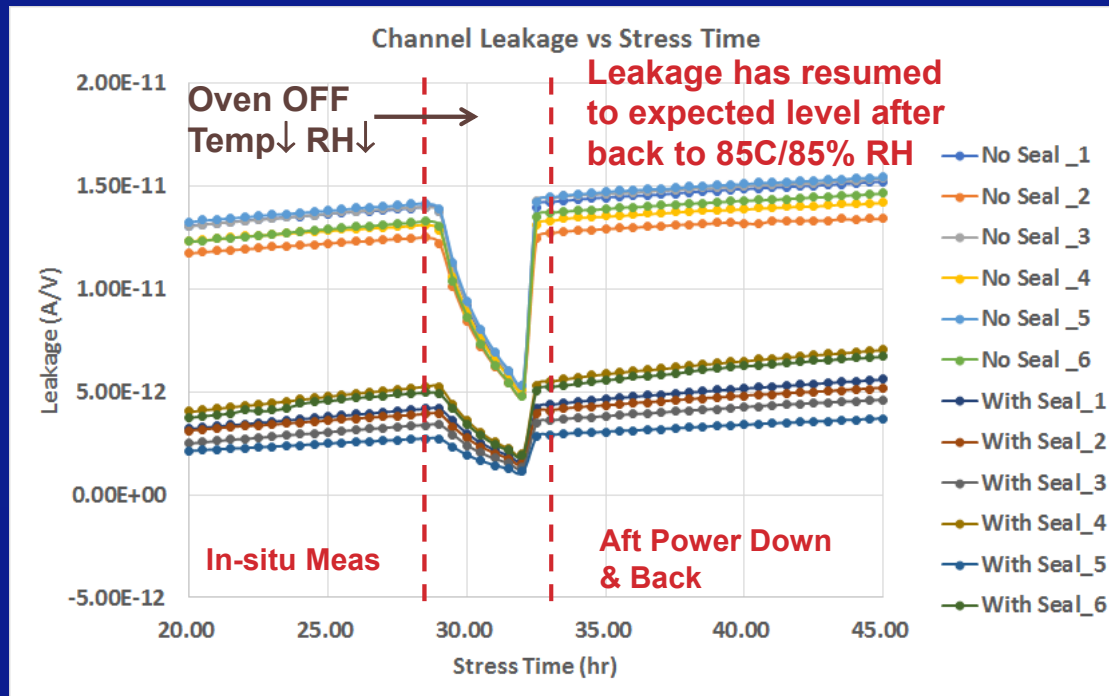
Oven is deliberately powered down at 29th hour

- Current measurement continues throughout, with the DUT Board Setup in the Oven throughout
- Temp & RH dropped down to ambient conditions
- Channel leakages decreases with Temp↓ RH↓

Oven is re-powered on again at 34th hour

- Channel leakage starts to increase as the environment conditions goes back to 85°C/85%RH

In-Situ Electrical Measurements

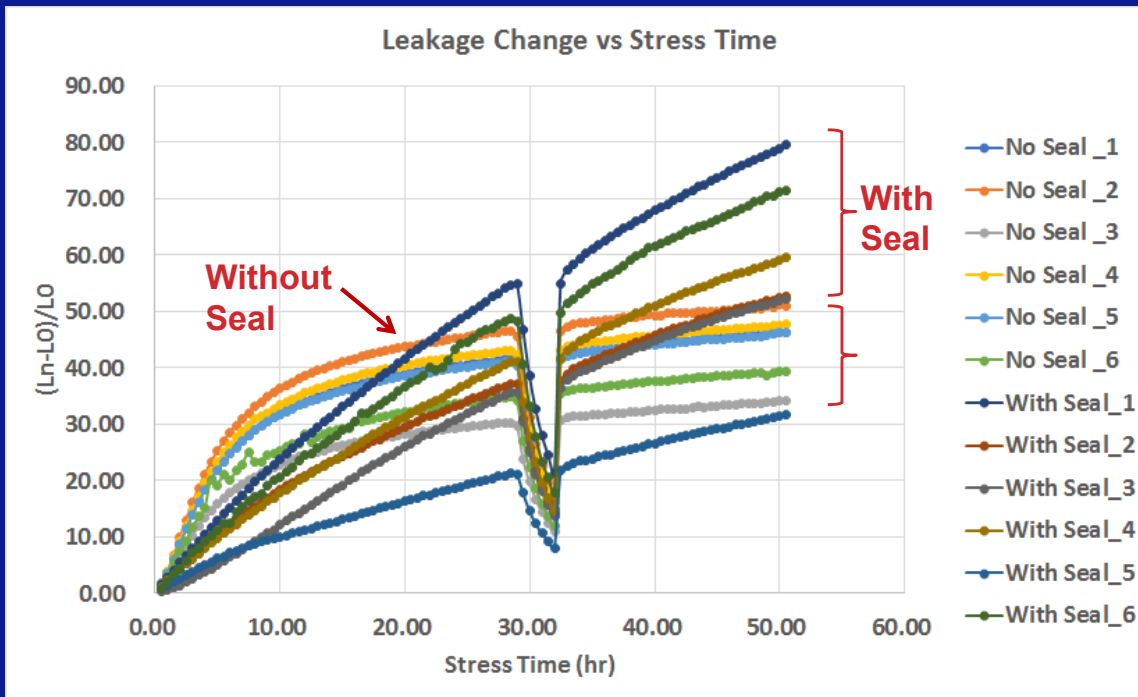


Channel leakage level goes back to the expected level for the Stress Time at the 85°C/85% RH test environment

This shows that:

- (a) In-situ measurements data can be well correlated with electrical data after power off
- (b) Real-time electrical analysis throughout HAST/THB Tests can be demonstrated

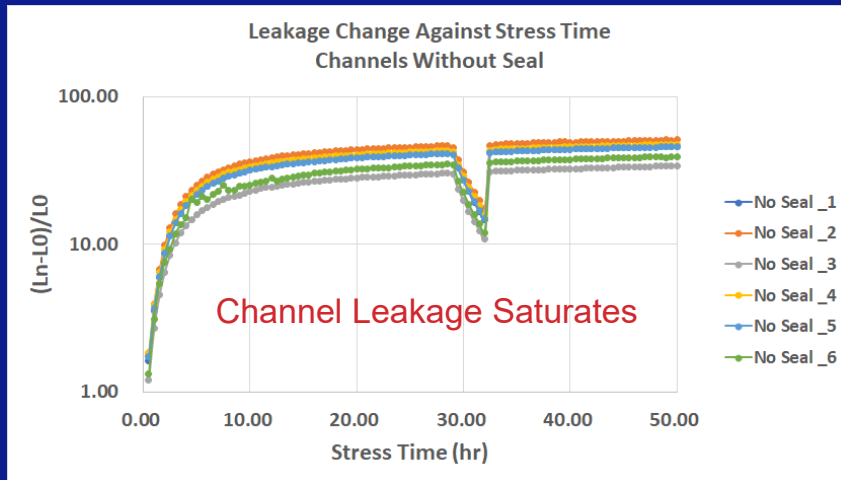
Will Leakage Increase with Stress Time ?



HAST/THB Tests are usually at high voltages, high temp with high humidity over long hours
 → Key: Will Channel Leakage increase with Stress Time at 85°C/85%RH?

Based on the data & results
 Channel Leakage
 (a) w/o Seal: Saturates 20hr
 (b) w Seal: Increasing trend but will saturate over time

Will Leakage Increase with Stress Time ?

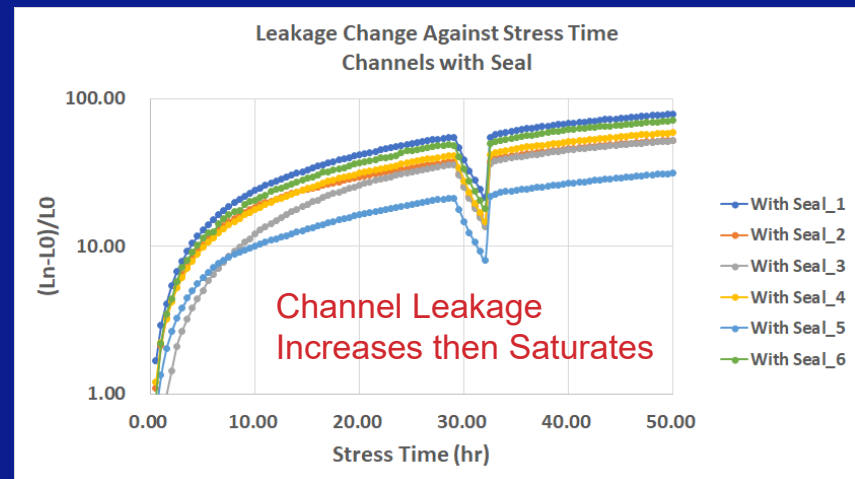


→ With Sealing

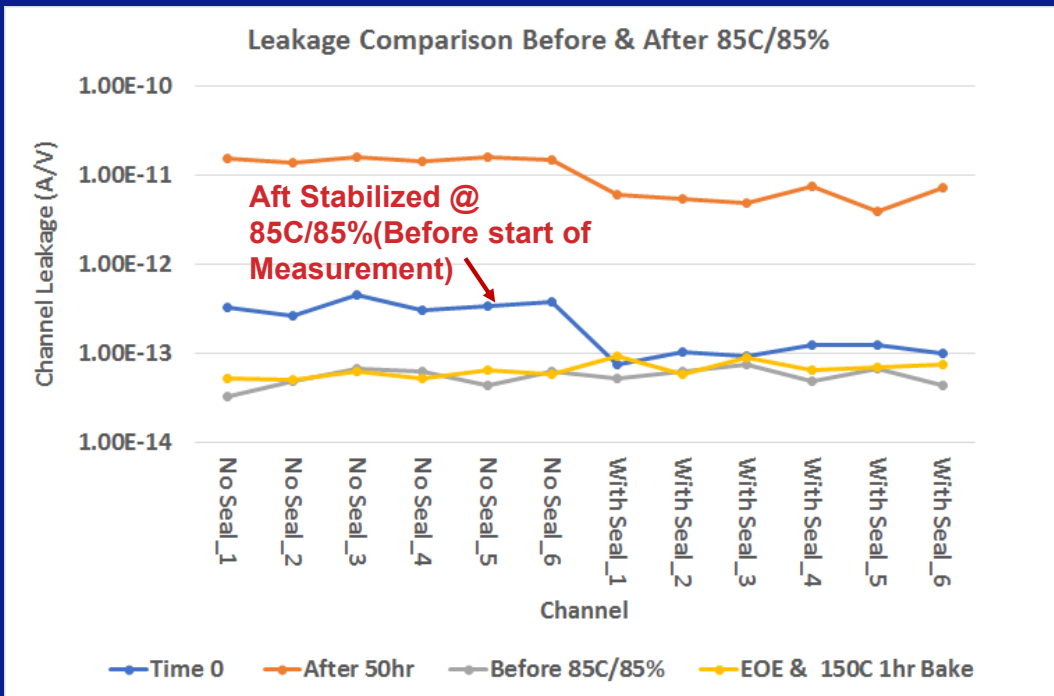
- Channel Leakage will increase then starts to saturate over Stress Time
- Based on data, saturation at 85°C/85% RH is beyond 50hrs (but will eventually saturate)

← Without Sealing

- Channel Leakage will saturate over Stress Time
- Based on data, saturation point at 85°C/85% RH is around 20hrs



No Degradation Observed on the DUT Board



Humidity is the key parameter causing the increase in leakage throughout the 85°C/85% RH Test

Results shows

- Channel leakage of the board before and after the 85°C/85% RH Test remains good

- There is no damage / degradation to the DUT Board Setup throughout the 85°C/85% RH Test
- The increase in Channel Leakage over time is environment driven and not DUT Board Setup materials driven

Results

- Channel Leakage Level
 - pico-Ampere current measurements have been achieved with the DUT board, Socket & cable assembly setup
 - Channel leakage can be reduced down to sub pA level with Sealing
- Channel leakage current recovers to expected level after Power Off & On
 - In-situ measurement data can correlate with traditional method of power off and doing electrical measurements using an external system
- Channel Leakage will saturate over Stress Time
 - Without Seal: Increase & saturates after approx. 20hrs
 - With Seal: Increases & saturates after approx. 50hrs
- There is minimal degradation on the DUT board after 85°C/85% RH Test

Conclusions

- Qualified set of DUT Board, Socket & Cable Assembly has been demonstrated to be capable of providing low level current measurements
- Consistent pA level electrical measurements have been demonstrated over prolonged burn-in stress tests
- Real time in-situ electrical measurements at low-level pico-A current through HAST/THB Test has been demonstrated to be achievable

Acknowledgements

- The authors would like to acknowledge the support and help rendered by MFG for the production & fabrication of the fixtures used in the experiments

COPYRIGHT NOTICE

The presentation(s)/poster(s) in this publication comprise the Proceedings of the 2019 TestConX China workshop. The content reflects the opinion of the authors and their respective companies. They are reproduced here as they were presented at the 2019 TestConX China workshop. This version of the presentation or poster may differ from the version that was distributed in hardcopy & softcopy form at the 2019 TestConX China workshop. The inclusion of the presentations/posters in this publication does not constitute an endorsement by TestConX or the workshop's sponsors.

There is NO copyright protection claimed on the presentation/poster content by TestConX. However, each presentation/poster is the work of the authors and their respective companies: as such, it is strongly encouraged that any use reflect proper acknowledgement to the appropriate source. Any questions regarding the use of any materials presented should be directed to the author(s) or their companies.

The TestConX China logo and TestConX logo are trademarks of TestConX. All rights reserved.

www.TestConX.org